PRELIMINARY

SFTX3501-3X-16Q

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

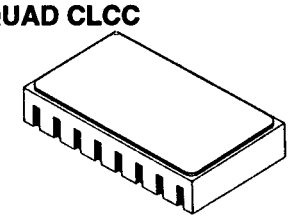
TRIPLE UNCOMMITTED 300mA 150 Volt NPN TRANSISTOR

Designer's Data Sheet

FEATURES:

- Eutectic Die Attach, Hermetic Package
- Electrical performance similar to 3 X 2N3501 in one package

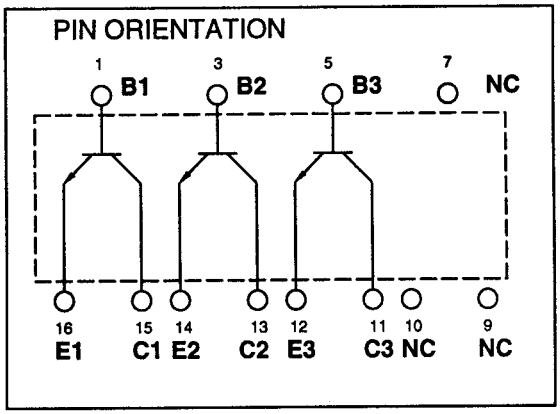
16 PIN QUAD CLCC

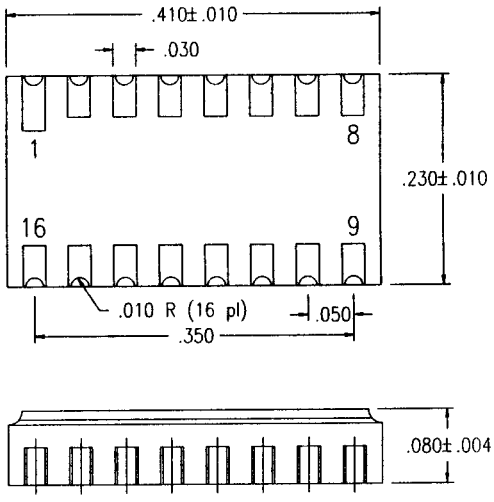


MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CEO}	150	V
Collector-Base Voltage	V_{CBO}	150	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current (per transistor)	I_C	300	mA
Total Device Dissipation @ TC= 25°C (All three transistors)	P_D	7.0	W
Operating and Storage Temperature	Tj, Tstj	-55 to +200	°C
Thermal Resistance, Junction to Case (all 3 transistors)	$R_{\theta JC}$	25	°C/W

PACKAGE OUTLINE: 16 PIN QUAD CLCC





NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: XN0023 D	MED

SFTX3501-3X-16Q

SOLID STATE DEVICES, INC
14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS (Per Transistor)@ T_A=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	MAX	UNIT
Collector-Emitter Breakdown Voltage (IC= 10.0mAdc, IB=0 A)		BV_{CEO}	150	---	V
Collector- Base Breakdown Voltage (IC= 10.0μAdc, IE=0 A)		BV_{CBO}	150	---	V
Emitter-Base Breakdown Voltage (IE = 10μAdc, IC=0 A)		BV_{EBO}	6	---	V
Collector-Base Cutoff Current (VCB= 75 Vdc, IE=0 A) (VCB=75 Vdc, IE=0A, TA=150°C)		I_{CBO}	--- ---	50 50	nA uA
Emitter Cutoff Current (VEB = 4 Vdc)		I_{EBO}	---	25	nA
DC Current Gain (IC= 0.1 mAdc, VCE= 10 Vdc) (IC= 150 mAdc, VCE= 10 Vdc) (IC=150mAdc, VCE=10Vdc, TA=150°C)		HFE	35 100 45	--- 300 ---	
Collector -Emitter Saturation Voltage (IC= 150 mAdc, IB = 15 mAdc)		$V_{CE(SAT)}$	---	0.4	V
Base-Emitter Saturation Voltage (IC= 150 mAdc, IB = 15 mAdc)		$V_{BE(SAT)}$	---	1.2	V
Output Capacitance (VCB= 10 Vdc, IE= 0 Adc, f=1MHz)		Cob	---	10	pF
Input Capacitance	(VBE= 0.5 Vdc, IC= 0 Adc, f=1MHz)	Cib	---	80	pF
On Time	**IC= 150 mAdc Vcc=100Vdc IB1=15 mAdc VEB=-2 Vdc**	ton	---	115	nsec
Off Time	**IC=150mA Vcc=100Vdc IB1= -IB2=15 mAdc**	toff	---	1150	

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.